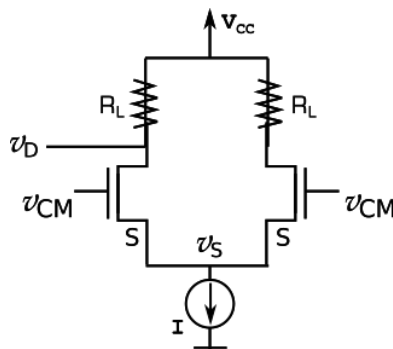


CSU0007 Basic Electronics, Homework 7

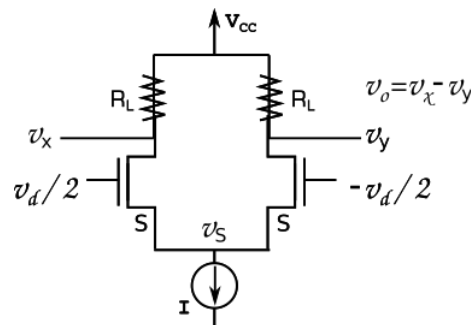
- Submit your work via Moodle before **5PM, Jan. 14th**. The solution will be available right after for you to prepare for the final exam on Jan. 15th.

1. (50 points) For the following difference amplifier, suppose that $I=0.64\text{mA}$, $V_{CC}=3\text{V}$, $R_L=2\text{k}\Omega$, $K=1\text{mA/V}^2$, $V_T=1\text{V}$, and $v_{CM}=2\text{V}$.

- (40 points) Suppose that both MOSFET operates under the saturation discipline. Compute large signals v_D and v_S .
- (10 points) Determine the maximum possible v_{CM} for both MOSFET to remain in saturation.



2. (30 points) In class, we've shown that $A_d = \frac{v_o}{v_d} = -g_m R_L$ for a difference amplifier:

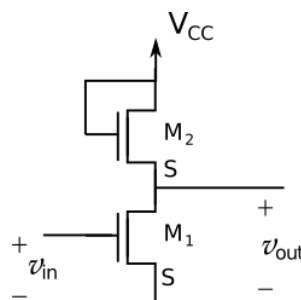


Now, assuming both MOSFETs are identical, show that, approximately, $A_d = -R_L \sqrt{K} \sqrt{I}$.

Hint: Consider that current $I/2 + \Delta i$ flowing through the left MOSFET and that current $I/2 - \Delta i$ flowing through the right MOSFET, where Δi is of a small quantity.

This result gives us an insight: in order to improve the small-signal voltage gain, we may choose to increase I the biasing current. In this way we keep R_L the same, and thus the output resistance remains unchanged :)

3. (20 points) We've learned a way to wire a MOSFET for it to work like a resistor for a small-signal. Now, consider the following inverting amplifier, with the load resistor replaced by MOSFET M_2 (with parameter $K = K_2$). Suppose that M_1 (with parameter $K = K_1$) operates under the saturation discipline:



Show that the small-signal voltage gain, $\frac{v_{out}}{v_{in}}$, is equal to $-\sqrt{\frac{K_1}{K_2}}$.

Hint: The same amount of current should flow through both M_1 and M_2 .

This result suggests a cool feature: recall that parameter K for a MOSFET is in portion to the geometric length (L) and width (W) of the channel between source and drain, i.e., $K = K'(\frac{W}{L})$. Assuming that the two MOSFETs have identical K' and L , then essentially, we may setup the voltage gain of this circuit by building the MOSFETs with the calculated relative channel widths :)